

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-8. (Canceled).

9. (Currently Amended) A vapor phase growth method, comprising performing a vapor phase growth of a silicon epitaxial layer on a main surface of a silicon single crystal substrate using a vapor phase growth apparatus, wherein:

the vapor phase growth apparatus comprises a susceptor for performing the vapor phase growth of the silicon epitaxial layer on the main surface of the silicon crystal substrate while heating the silicon single crystal substrate from both sides while the substrate is on a pocket formed on the susceptor;

the pocket has an outer peripheral side part which supports a rear surface of the silicon single crystal substrate and an inner peripheral side part which is kept in a state of being more recessed than the outer peripheral side part in an inside of the outer peripheral side part; and

the susceptor is formed by heat-treating a body section composed of graphite and then coating a surface of the body section with SiC, and is formed so that an entirety of a longitudinal sectional shape of the susceptor is warped to an inverted U-shape during the heat-treating and among the susceptors formed so that an entirety of the longitudinal sectional shape of the susceptor is warped to an inverted U-shape or to an U-shape during the heat-treating, the susceptor which is warped to the inverted U-shape is selected to be used.

10. (Previously Presented) The vapor phase growth method as claimed in claim 9, wherein

the pocket is formed for the silicon single crystal substrate having a diameter of 300 mm or more, and

when the silicon single crystal substrate is placed on and supported by the outer peripheral side part of the susceptor, a maximum distance between a bottom surface of the inner peripheral side part in the pocket and a rear surface of the silicon single crystal substrate is less than 0.4 mm.

11. (Previously Presented) The vapor phase growth method as claimed in claim 9, wherein

the susceptor is a type of a single wafer, and
a curvature on a rear surface side of the susceptor is $1.75 \times 10^{-5} \text{ mm}^{-1}$ or less.

12. (Previously Presented) A vapor phase growth method as claimed in claim 10, wherein

the susceptor is a type of a single wafer, and
a curvature on a rear surface side of the susceptor is $1.75 \times 10^{-5} \text{ mm}^{-1}$ or less.

13-14. (Canceled)

15. (Previously Presented) The vapor phase growth method as claimed in claim 9, wherein

a depth of the pocket has been reduced by a warp amount during the heat-treatment warping of the inverted U-shaped longitudinal sectional shape.

16. (Previously Presented) The vapor phase growth method as claimed in claim 15, wherein

the pocket is formed for the silicon single crystal substrate having a diameter of 300 mm or more, and

when the silicon single crystal substrate is placed on and supported by the outer peripheral side part of the susceptor, a maximum distance between a bottom surface of the inner peripheral side part in the pocket and a rear surface of the silicon single crystal substrate is less than 0.4 mm.

17-19. (Canceled)